

# SEMICONDUCTOR DEVICE AND ITS FABRICATING PROCESS

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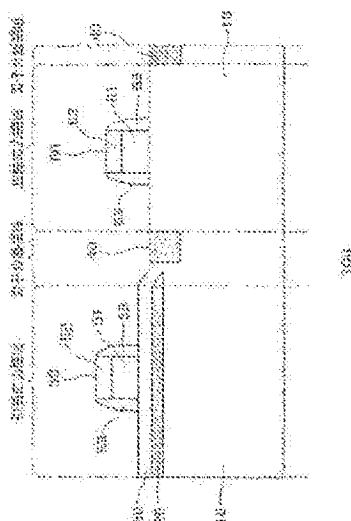
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## Abstract of JP 2004047806 (A)

**PROBLEM TO BE SOLVED:** To provide a semiconductor device equipped with semiconductor elements in which stress of a region where the semiconductor elements are formed is controlled to improve mobility of electric charges, to provide its fabricating process and further to provide a semiconductor device fabricating process in which less crystal defect and less crystal transition are generated in a semiconductor element forming region even if a SOI structure is partially formed, and furthermore to provide the semiconductor device fabricated by the process. ; **SOLUTION:** The semiconductor device is provided with a semiconductor substrate 10, a first region that covers continuously an insulating layer 20 and its upper portion that are partially provided on a surface of the semiconductor substrate 10 and includes a semiconductor layer 30 at least whose one end is connected to the semiconductor substrate 10, a second region in which the first region is near thereto and there exists no insulating layer 20 near the surface of the semiconductor substrate 10, and a first semiconductor element 50 formed in the semiconductor layer 30 on the insulating layer 20 in the first region. ; **COPYRIGHT:** (C)2004,JPO



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